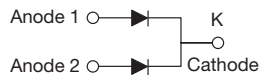
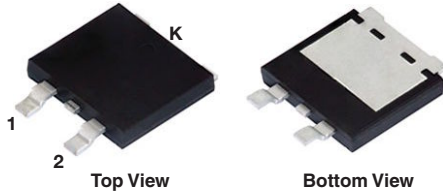


Hyperfast Rectifier, 2 x 10 A FRED Pt[®]

eSMP[®] Series SMPD (TO-263AC)



FEATURES

- Hyperfast recovery time, reduced Q_{rr} , and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

DESIGN SUPPORT TOOLS AVAILABLE



3D Models

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_R	200 V
V_F at I_F	0.77 V
t_{rr}	25 ns
T_J max.	175 °C
Package	SMPD (TO-263AC)
Circuit configuration	Common cathode

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, telecom, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current	$I_{F(AV)}$	$T_{\text{solder pad}} = 152\text{ °C}$	20	A
			per device	
Non-repetitive peak surge current	I_{FSM}	$T_J = 25\text{ °C}$, 6 ms square pulse	210	
			per diode	

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_R	$I_R = 100\ \mu\text{A}$	200	-	-	V
Forward voltage, per diode	V_F	$I_F = 10\text{ A}$	-	0.94	1.05	
		$I_F = 10\text{ A}$, $T_J = 150\text{ °C}$	-	0.77	0.87	
Reverse leakage current, per diode	I_R	$V_R = V_R$ rated	-	-	2	μA
		$T_J = 150\text{ °C}$, $V_R = V_R$ rated	-	10	150	
Junction capacitance, per diode	C_T	$V_R = 200\text{ V}$	-	30	-	pF



DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$I_F = 1\text{ A}$, $di_F/dt = 50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	25	-	ns
		$I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{rr} = 0.25\text{ A}$	-	-	25	
		$T_J = 25\text{ }^\circ\text{C}$	-	22	-	
		$T_J = 125\text{ }^\circ\text{C}$	-	35	-	
Peak recovery current	I_{RRM}	$T_J = 25\text{ }^\circ\text{C}$	-	2.5	-	A
		$T_J = 125\text{ }^\circ\text{C}$	-	5	-	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$	-	25	-	nC
		$T_J = 125\text{ }^\circ\text{C}$	-	85	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-55	-	+175	$^\circ\text{C}$
Thermal resistance, per diode junction to solder pad	R_{thJ-Sp}		-	1.8	2.4	$^\circ\text{C}/\text{W}$
Approximate weight			0.55			g
			0.02			oz.
Marking device		Case style SMPD (TO-263AC)	20CDH02			

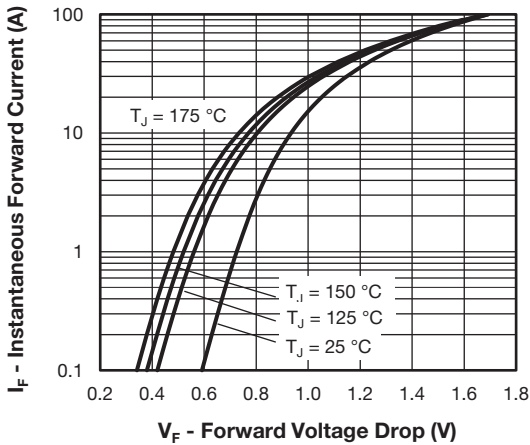


Fig. 1 - Typical Forward Voltage Drop Characteristics

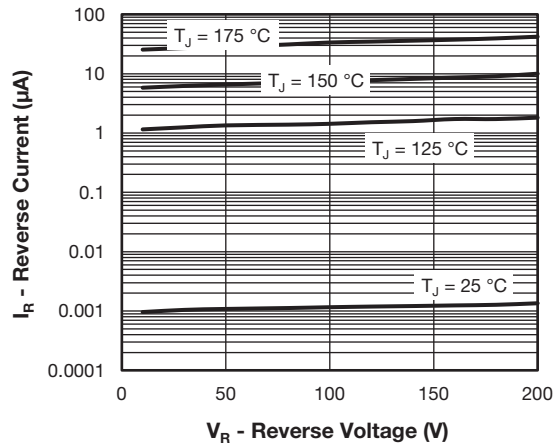


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

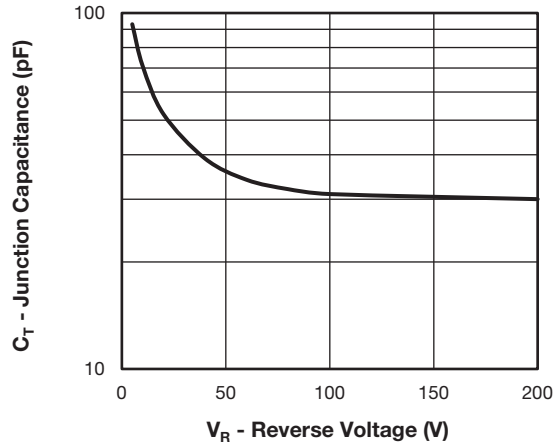


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

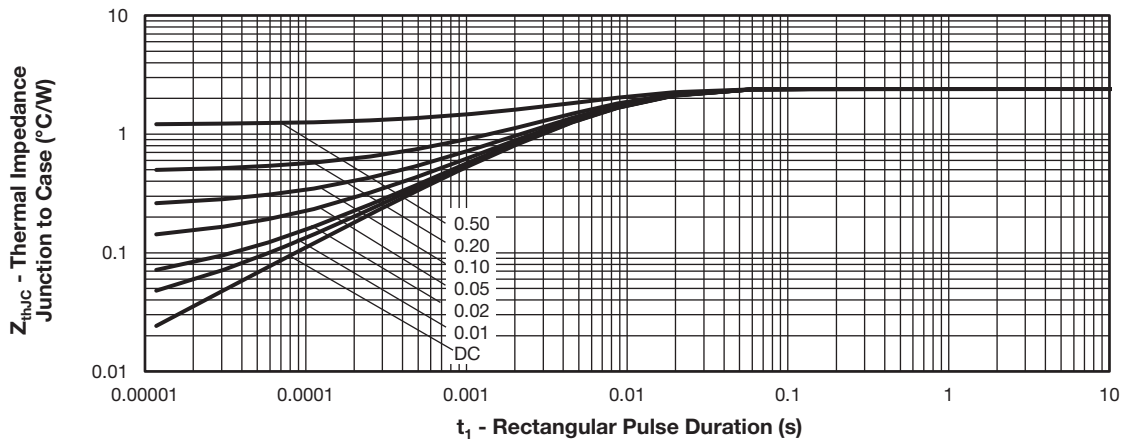


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

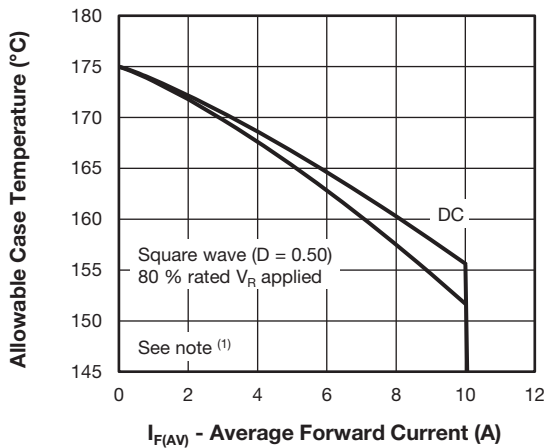


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

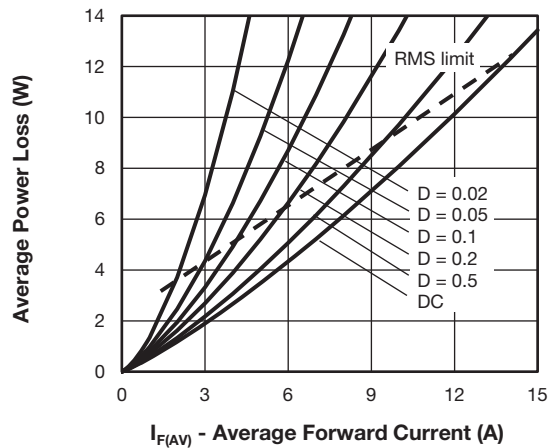


Fig. 6 - Forward Power Loss Characteristics

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 P_d = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5);
 P_{dREV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

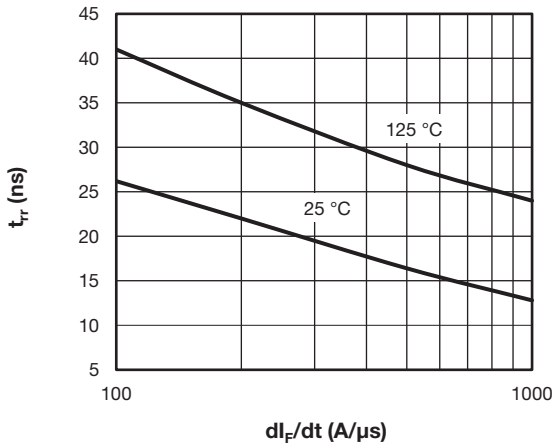


Fig. 7 - Typical Reverse Recovery Time vs. di_F/dt

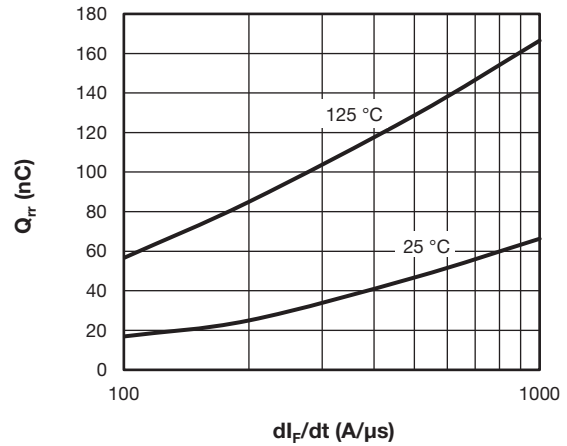
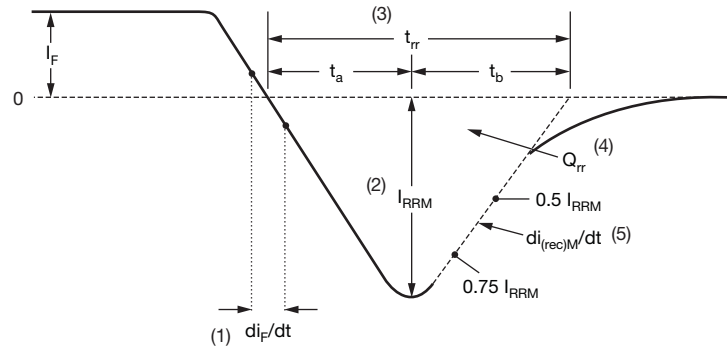


Fig. 8 - Typical Stored Charge vs. di_F/dt



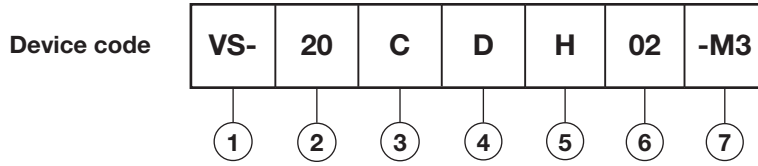
- (1) di_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Current rating (20 A)
- 3** - Circuit configuration:
C = common cathode
- 4** - D = SMPD package
- 5** - Process type,
H = hyperfast recovery
- 6** - Voltage code (02 = 200 V)
- 7** - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

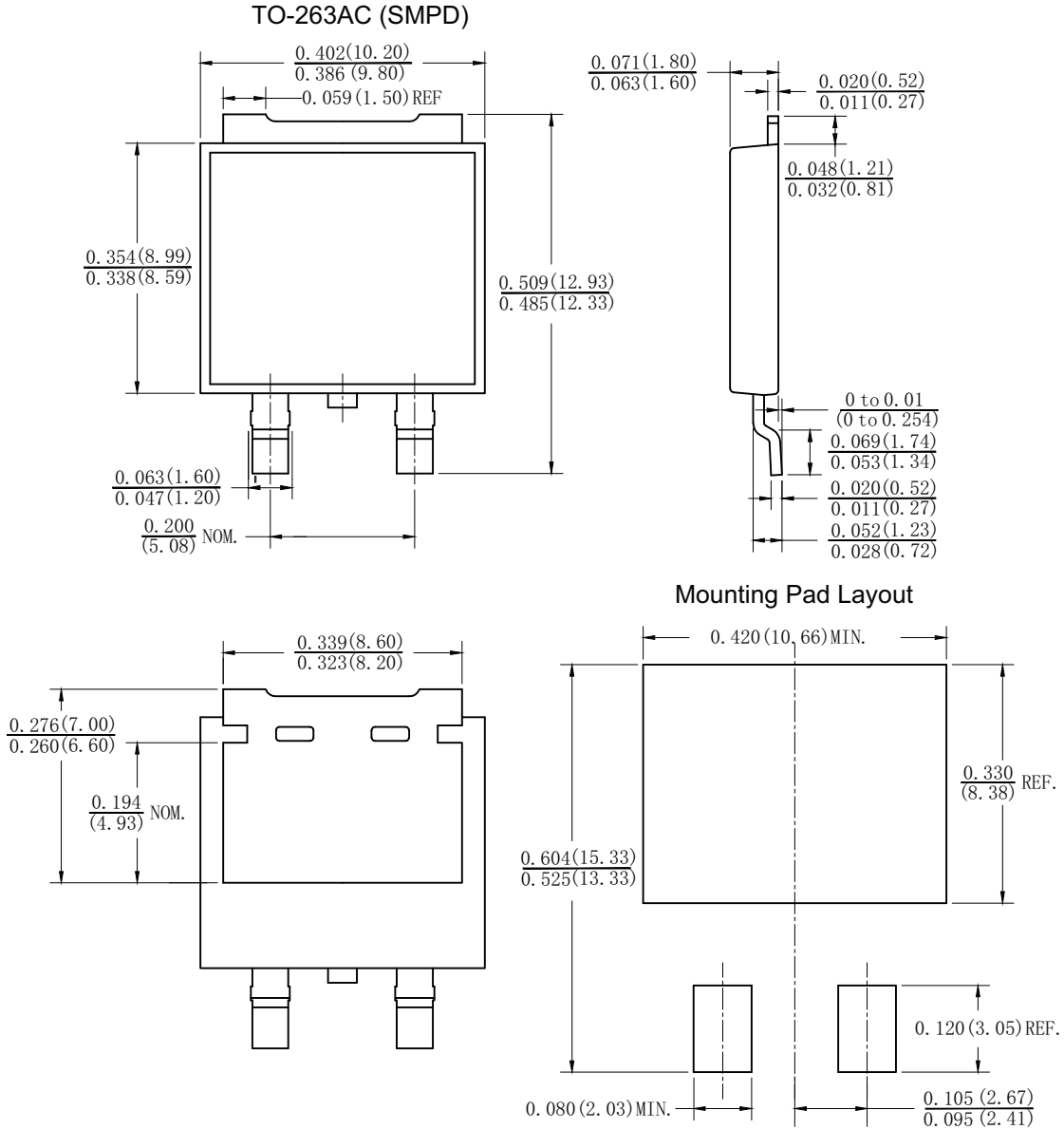
ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-20CDH02-M3/I	2000	2000	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95604
Part marking information	www.vishay.com/doc?95566
Packaging information	www.vishay.com/doc?88869
SPICE model	www.vishay.com/doc?96572



TO-263AC (SMPD)

DIMENSIONS in inches (millimeters)





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